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(54) SEMICONDUCTOR STRUCTURE AND MANUFACTURING METHOD THEREOF

(71) Applicant: CHANGXIN MEMORY

TECHNOLOGIES, INC., Hefei City

(72) Inventors: Yutong SHEN, Hefei City (CN); Jifeng

TANG, Hefei City (CN)

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ABSTRACT (57)

The present disclosure provides a semiconductor structure and a manufacturing method thereof, and relates to the technical field of semiconductors. The semiconductor structure includes: a base, including a doped region; a recess, located in the doped region; and a gradient layer, filling the recess, wherein a doping concentration of the gradient layer varies gradually from a bottom of the recess upwards.

